



100V N-Channel Enhancement Mode MOSFET

Voltage

100 V

Current

50 A

Features

- R_{DS(ON)}, V_{GS}@10V,I_D@30A<22mΩ
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

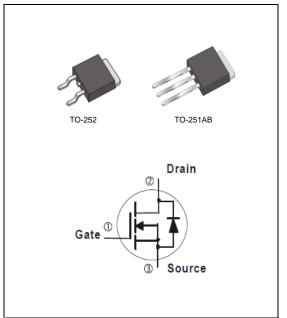


• Case: TO-251AB, TO-252 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• TO-251AB Approx. Weight: 0.0104 ounces, 0.297grams

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Maximum Ratings and Thermal Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	100	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	I _D	50	А	
	T _C =100°C		32		
Pulsed Drain Current	T _C =25°C	I _{DM}	100		
Power Dissipation	T _C =25°C	Po	96	10/	
	T _C =100°C		38	W	
Continuous Drain Current	T _A =25°C	I _D	8	А	
	T _A =70°C		6.5	Α	
Power Dissipation	T _A =25°C		2.5	W	
Power Dissipation	T _A =70°C	Pb	1.6		
Single Pulse Avalanche Energy (Note 1)		E _{AS}	80	mJ	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C	
Typical Thermal Resistance	Junction to Case	$R_{ heta JC}$	1.3	°C/W	
	Junction to Ambient	$R_{\theta JA}$	50 ^(Note 1)		

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	100	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	2.5	3.57	4.5	V		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =30A	-	18.3	22	mΩ		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =80V,V _{GS} =0V	-	0.01	1.0	uA		
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	<u>+</u> 10	<u>+</u> 100	nA		
Dynamic (Note 5)								
Total Gate Charge	Qg	. V . E0.V I . 20.A	-	29	-	nC		
Gate-Source Charge	Q_{gs}	V_{DS} =50V, I_{D} =30A, V_{GS} =10V (Note 2,3)	-	9.5	-			
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	10	-			
Input Capacitance	Ciss	\/ 45\/\/ O\/	-	1643	-	pF		
Output Capacitance	Coss	V_{DS} =15V, V_{GS} =0V, f =1.0MHZ	-	257	-			
Reverse Transfer Capacitance	Crss	I=1.0WITZ	-	63	-			
Turn-On Delay Time	td _(on)		-	19	-	ns		
Turn-On Rise Time	t _r	V _{DD} =50V, I _D =30A,	-	56	-			
Turn-Off Delay Time	td _(off)	V_{GS} =10V, R_{G} =3 Ω (Note 2,3)	-	25	-			
Turn-Off Fall Time	t _f		-	13	-			
Drain-Source Diode								
Maximum Continuous Drain-Source	I _S		-	-	50	А		
Diode Forward Current								
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	-	0.67	1.0	V		
Reverse Recovery Time	trr	V _{GS} =0V, I _S =20A	_	31	-	ns		
Reverse Recovery Charge	Qrr	dI _F / dt=100A/us (Note 2)	-	38	-	uC		

NOTES:

- 1. The test by surface mounted on 1 inch FR4 board with 2oz copper.
- 2. L=0.1mH, I_{AS} =40A, V_{DD} =25V, V_{GS} =10V, R_{G} =25ohm, Starting T_{J} =25°C
- 3. The Power dissipation is limit by 150°C junction temperature.
- 4. Pulse width<a>300us, Duty cycle<a>2%
- 5. Guaranteed by design, not subject to production testing





TYPICAL CHARACTERISTIC CURVES

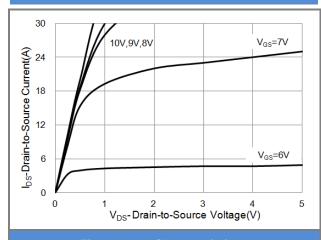


Fig.1 Output Characteristics

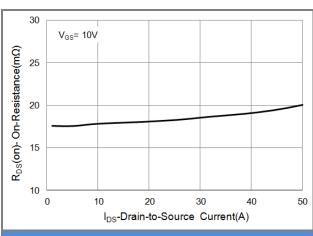
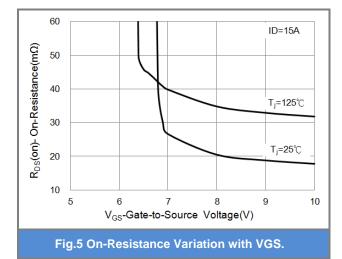


Fig.3 On-Resistance vs. Drain Current



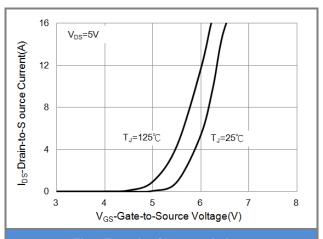


Fig.2 Transfer Characteristics

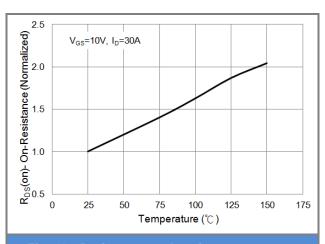


Fig.4 On-Resistance vs. Junction temperature

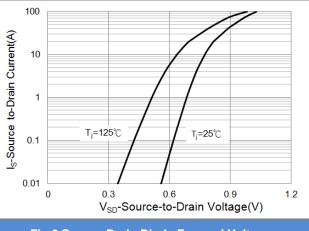


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

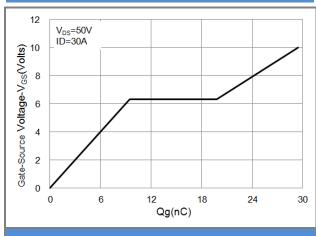
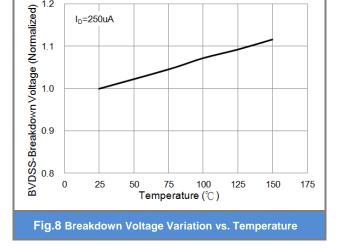


Fig.7 Gate-Charge Characteristics



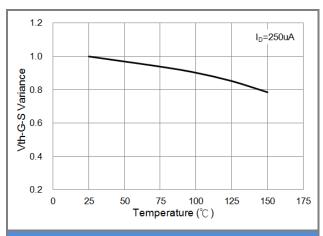


Fig.9 Threshold Voltage Variation with Temperature

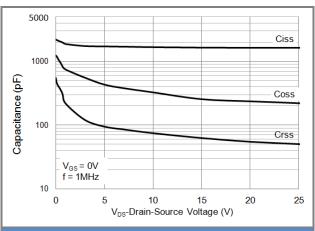
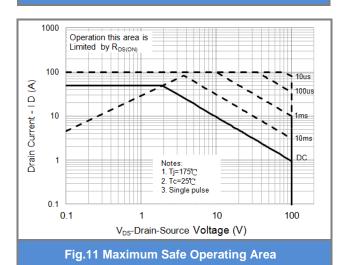


Fig.10 Capacitance vs. Drain-Source Voltage







TYPICAL CHARACTERISTIC CURVES

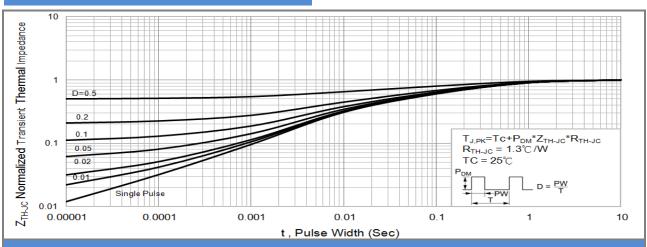
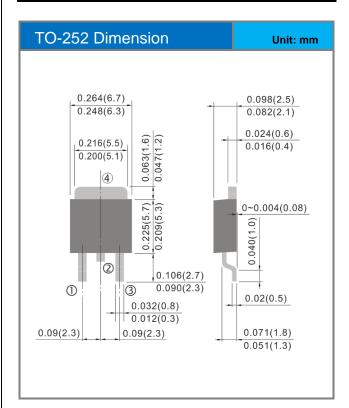


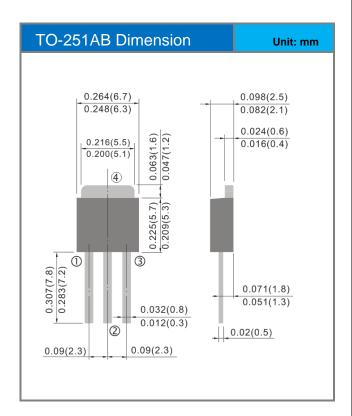
Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width





Packaging Information





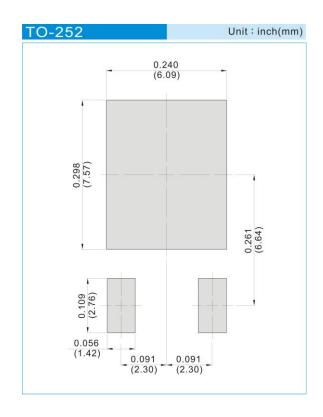




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJD50N10L_L2_00001	TO-252	3,000pcs / 13" reel	D50N10L	Halogen free
PJU50N10L_T0_00001	TO-251AB	80pcs / Tube	U50N10L	Halogen free

MOUNTING PAD LAYOUT







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